



Complete 10 μ s CMOS 12-Bit ADC

MAX172

General Description

The MAX172 is a complete 12-Bit analog-to-digital converter (ADC) that combines high speed, low power consumption, and an on-chip voltage reference. The conversion time is 10 μ s. The buried zener reference provides low drift and low noise performance.

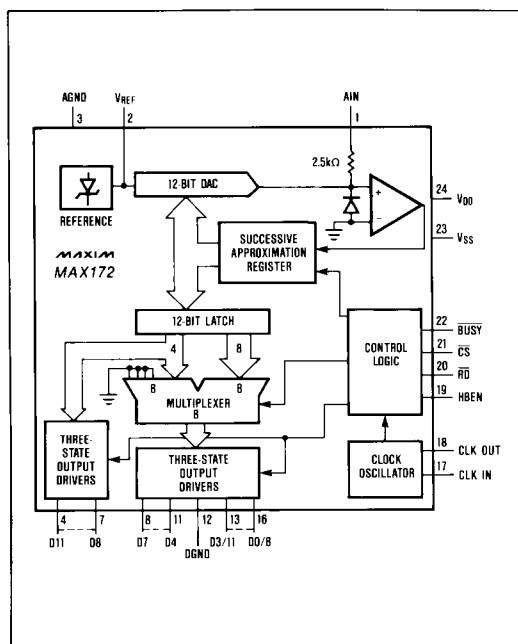
External component requirements are limited to only decoupling capacitors for the power supply and reference voltages. On-chip clock circuitry is also included which can either be driven from an external source, or in stand-alone applications, can be used with a crystal.

The MAX172 uses a standard microprocessor interface architecture. Three-state data outputs are controlled by Read (RD) and Chip Select (CS) inputs. Data access and bus release times of 90 and 75ns respectively ensure compatibility with most popular microprocessors without resorting to wait states.

Applications

Digital Signal Processing (DSP)
High Accuracy Process Control
High Speed Data Acquisition
Electro-Mechanical Systems

Functional Diagram



Features

- ◆ 12-Bit Resolution and Linearity
- ◆ 10 μ s Conversion Time
- ◆ No Missing Codes
- ◆ On-Chip Voltage Reference
- ◆ 90ns Access Time
- ◆ 215mW Max Power Consumption
- ◆ 24-Lead Narrow DIP Package
- ◆ Pin-for-Pin AD7572 Replacement

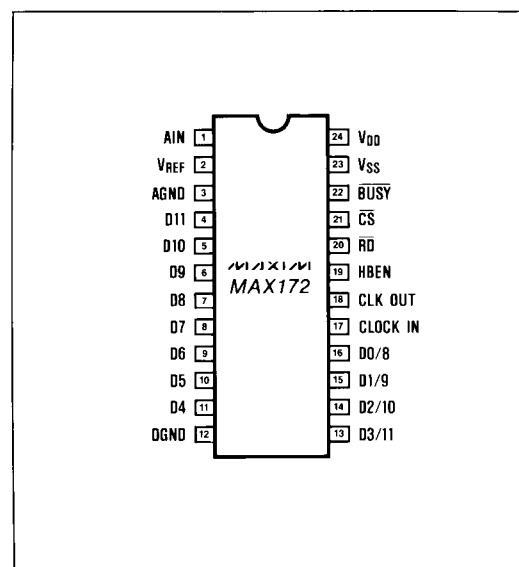
Ordering Information

PART	TEMP. RANGE	PACKAGE*	ERROR
MAX172ACNG	0°C to +70°C	Plastic DIP	$\pm 1/2$ LSB
MAX172BCNG	0°C to +70°C	Plastic DIP	± 1 LSB
MAX172ACWG	0°C to +70°C	Wide S.O.	$\pm 1/2$ LSB
MAX172BCWG	0°C to +70°C	Wide S.O.	± 1 LSB
MAX172CC/D	0°C to +70°C	Dice**	+1 LSB
MAX172AING	-25°C to +85°C	Plastic DIP	$\pm 1/2$ LSB
MAX172BING	-25°C to +85°C	Plastic DIP	+1 LSB
MAX172AMRG	-55°C to +125°C	CERDIP	$\pm 1/2$ LSB
MAX172BMRG	-55°C to +125°C	CERDIP	+1 LSB

* All devices — 24 lead packages

** Consult factory for dice specifications

Pin Configuration



Maxim Integrated Products 1

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ABSOLUTE MAXIMUM RATINGS

V_{DD} to DGND	-0.3V to +7V
V_{SS} to DGND	+0.3V to -17V
AGND to DGND	-0.3V, V_{DD} + 0.3V
AIN to AGND	-15V to +15V
Digital Input Voltage to DGND	-0.3V, V_{DD} + 0.3V (Pins 17, 19-21)
Digital Output Voltage to DGND	-0.3V, V_{DD} + 0.3V (pins 4-11, 13-16, 18, 22)

Operating Temperature Ranges

MAX172XC	0°C to +70°C
MAX172XI	-25°C to +85°C
MAX172XM	-55°C to +125°C
Storage Temperature Range	-65°C to +160°C
Power Dissipation (any Package) to +75°C	1000mW
Derates Above +75°C by	10mW/°C
Lead Temperature (Soldering 10 seconds)	+300°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(V_{DD} = +5V $\pm$ 5%, V_{SS} = -12V or -15V $\pm$ 5%; Slow Memory Mode; T_A = T_{MIN} to T_{MAX} unless otherwise noted, f_{CLK} = 1.25MHz.)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS	
ACCURACY								
Resolution					12		Bits	
Integral NonLinearity	INL	MAX172A	$T_A = 25^{\circ}\text{C}$			+ 1/2	LSB	
		MAX172AC/AI				+ 1/2		
		MAX172AM				+ 3/4		
		MAX172B				+ 1		
Differential NonLinearity	DNL	Guaranteed Monotonic Over Temp.				+ 1	LSB	
Offset Error (Note 1)		MAX172B	$T_A = 25^{\circ}\text{C}$ $T_A = T_{\text{MIN}}$ to T_{MAX}			± 4 ± 6	LSB	
		MAX172A	$T_A = 25^{\circ}\text{C}$ $T_A = T_{\text{MIN}}$ to T_{MAX}			± 3 ± 4		
Full Scale Error (Note 2)		MAX172B	$T_A = 25^{\circ}\text{C}$			+ 15	LSB	
		MAX172A	$T_A = 25^{\circ}\text{C}$			+ 10		
Full Scale Tempco (Notes 3, 4)						+ 45	ppm/°C	
ANALOG INPUT								
Input Voltage Range					0	5	V	
Input Current		AIN = 0V to +5V				3.5	mA	
INTERNAL REFERENCE								
VREF Output Voltage		$T_A = 25^{\circ}\text{C}$			-5.2	-5.25	-5.3	V
VREF Output Tempco (Note 5)						40		ppm/°C
Output Current Sink Capability		(Note 6)					500	μA
LOGIC INPUTS								
Input Low Voltage	VIL	CS, RD, HBEN, CLKIN					0.8	V
Input High Voltage	VIH	CS, RD, HBEN, CLKIN			2.4			V
Input Capacitance (Note 7)	CIN	CS, RD, HBEN, CLKIN					10	pF
Input Current	IIN	CS, RD, HBEN CLKIN	VIN = 0 to VDD				+ 10 + 20	μA
LOGIC OUTPUTS								
Output Low Voltage	VOL	D11-D0/8, BUSY, CLKOUT ISINK = 1.6mA					0.4	V
Output High Voltage	VOH	D11-D0/8, BUSY, CLKOUT ISOURCE = 200μA			4			V
Floating State Leakage Current	ILKG	D11-D0/8, VOUT = 0V to VDD					+ 10	μA
Floating State Output Capacitance (Note 7)	COUT						15	pF

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ELECTRICAL CHARACTERISTICS (Continued)

(V_{DD} = +5V $\pm$ 5%, V_{SS} = -12V or -15V $\pm$ 5%; Slow Memory Mode; T_A = T_{MIN} to T_{MAX} unless otherwise noted, f_{CLK} = 1.25MHz.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
CONVERSION TIME						
MAX172	t _{CONV}	Synchronous (12.5 clock cycles) Asynchronous (12 to 13 clock cycles)	9.6		10 10.4	μ s
POWER SUPPLY REJECTION						
V _{DD} Only		FS Change, V _{SS} = -15V, V _{DD} = 4.75V to 5.25V		$\pm 1/2$		LSB
V _{SS} Only		FS Change, V _{DD} = 5V, V _{SS} = -5% to +5%		$\pm 1/8$		LSB
POWER REQUIREMENTS						
V _{DD}		$\pm 5\%$ for Specified Performance		5		V
V _{SS} (Note 8)		$\pm 5\%$ for Specified Performance		-12 or -15		V
I _{DD}		CS = RD = V _{DD} , AIN = 5V		5	7	mA
I _{SS}		CS = RD = V _{DD} , AIN = 5V		8	12	mA
Power Dissipation		V _{DD} = +5V, V _{SS} = -15V		145	215	mW

Note 1: Typical change over temp is +1 LSB.

Note 2: V_{DD} = +5V, V_{SS} = -15V, FS = +5.000V, Ideal last code transition = FS - 3/2LSB.

Note 3: Full Scale TC = Δ FS/ Δ T, where Δ FS is full scale change from T_A = 25°C to T_{MIN} or T_{MAX}.

Note 4: Includes internal reference drift.

Note 5: V_{REF} TC = Δ V_{REF}/ Δ T, where Δ V_{REF} is reference voltage change from T_A = 25°C to T_{MIN} or T_{MAX}.

Note 6: Output current should not change during conversion.

Note 7: Guaranteed by design, not subject to test.

Note 8: Functional operation at V_{SS} = -12V $\pm$ 5% is guaranteed by testing offset error and full scale error.

TIMING CHARACTERISTICS (Note 9)

(V_{DD} = +5V, V_{SS} = -12V or -15V; T_A = T_{MIN} to T_{MAX} unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	T _A = 25°C			MAX172C/I		MAX172M		UNITS
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
CS to RD Setup Time	t ₁		0			0		0		ns
RD to BUSY Delay	t ₂	C _L = 50pF		90	190		230		270	ns
Data Access Time (Note 10)	t ₃	C _L = 20pF C _L = 100pF		60 70	90 125		110 150		120 170	ns
RD Pulse Width	t ₄			t ₃			t ₃		t ₃	
CS to RD Hold Time	t ₅		0			0		0		ns
Data Setup Time After BUSY Note (10)	t ₆				70		90		100	ns
Bus Relinquish Time (Note 11)	t ₇		20		75	20	85	20	90	ns
HBEN to RD Setup Time	t ₈		0			0		0		ns
HBEN to RD Hold Time	t ₉		0			0		0		ns
Delay Between Read Operations	t ₁₀		200			200		200		ns

Note 9: Timing specifications are sample tested at 25°C to ensure compliance. All input control signals are specified with t_r = t_f = 5ns (10% to 90% of +5V) and timed from a voltage level of +1.6V.

Note 10: t₃ and t₆ are measured with the load circuits of Figure 1 and defined as the time required for an output to cross 0.8V or 2.4V.

Note 11: t₇ is defined as the time required for the data lines to change 0.5V when loaded with the circuits of Figure 2.

For additional information on using the MAX172 please refer to MAX162 data sheet.

